ABSTRACT OF THE DISCLOSURE

A photoelectric conversion device comprising at least an electron acceptive charge transfer layer, an electron donative charge transfer layer, and a light absorption layer existing between the charge transfer layers, wherein either one of the charge transfer layers comprises a semiconductor acicular crystal layer comprising aggregate of acicular crystals or a mixture of an acicular crystal and another crystal, and a method of producing the device are disclosed. Consequently, a photoelectric conversion device being capable of smoothly carrying out transfer of electrons and having high photoelectric conversion efficiency is provided.